TISP4070J3BJ THRU TISP4395J3BJ



BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

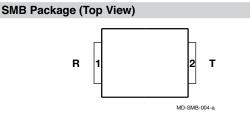
TISP4xxxJ3BJ Overvoltage Protector Series

Ion-Implanted Breakdown Region -Precise and Stable Voltage -Low Voltage Overshoot Under Surge

Designed for Transformer Center Tap (Ground Return) Overvoltage Protection -Enables GR-1089-CORE Compliance -High Holding Current Allows Protection of Data Lines with d.c. Power Feed

Can be Used to Protect Rugged Modems Designed for Exposed Applications Exceeding TIA-968-A

Device Name	V _{DRM} V	V _(BO) V
TISP4070J3BJ	58	70
TISP4080J3BJ	65	80
TISP4095J3BJ	75	95
TISP4115J3BJ	90	115
TISP4125J3BJ	100	125
TISP4145J3BJ	120	145
TISP4165J3BJ	135	165
TISP4180J3BJ	145	180
TISP4200J3BJ	155	200
TISP4219J3BJ	180	219
TISP4250J3BJ	190	250
TISP4290J3BJ	220	290
TISP4350J3BJ	275	350
TISP4395J3BJ	320	395



Device Symbol





Rated for International Surge Wave Shapes

Wave Shape	Standard	I _{PPSM} A
2/10	GR-1089-CORE	1000
8/20	IEC 61000-4-5	800
10/160	TIA-968-A	400
10/700	ITU-T K.20/21/45	350
10/560	TIA-968-A	250
10/1000	GR-1089-CORE	200

FL°

.....UL Recognized Component

Description

The range of TISP4xxxJ3BJ devices are designed to limit overvoltages on telecom lines. The TISP4xxxJ3BJ is primarily designed to address GR-1089-CORE compliance on data transmission lines with d.c. power feeding. When overvoltage protection is applied to transformer coupled lines from the transformer center tap to ground, the total ground return current can be 200 A, 10/1000 and 1000 A, 2/10. The high 150 mA holding current is set above common d.c. feed system levels to allow the TISP4xxxJ3BJ to reset following a disturbance.

These devices allow signal voltages, without clipping, up to the maximum off-state voltage value, V_{DRM} , see Figure 1. Voltages above V_{DRM} are limited and will not exceed the breakover voltage, $V_{(BO)}$, level. If sufficient current flows due to the overvoltage, the device switches into a low voltage on-state condition, which diverts the current from the overvoltage through the device. When the diverted current falls below the holding current, I_H, level the devices switches off and restores normal system operation.

How to Order

Device	Package	Carrier	Order As	Marking Code	Std. Qty.
TISP4xxxJ3BJ	SMB (DO-214AA)	Embossed Tape Reeled	TISP4xxxJ3BJR-S	4xxxJ3	3000

Insert xxx value corresponding to device name.

*RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

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Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

Rating		Symbol	Value	Unit
	'4070J3BJ		±58	
	'4080J3BJ		±65	
	'4095J3BJ		±75	v
4125J3 (4145J3) (4145J3) (4165J3) (4165J3) (4180J3) (4180J3) (4200J3) (4200J3)	'4115J3BJ		±90	
	'4125J3BJ		±100	
	'4145J3BJ		±120	
	'4165J3BJ	V	±135	
	'4180J3BJ	V _{DRM}	±145	
	'4200J3BJ		±155	
	'4219J3BJ		±180	
	'4250J3BJ		±190	
	'4290J3BJ		±220	
	4350J3BJ		±275	
	'4395J3BJ	<u> </u>	±320	
Non-repetitive peak impulse current (see Notes 1 and 2)				
2/10 μs (GR-1089-CORE, 2/10 μs voltage wave shape)			±1000	
8/20 μs (IEC 61000-4-5, combination wave generator, 1.2/50 μsvoltage wave shape)			±800	
10/160 µs (TIA-968-A, 10/160 µs voltage wave shape)			±400	
4/250 μs (ITU-T K.20/21, 10/700 μs voltage waveshape, simultaneous)		I _{PPSM}	±370	Α
5/310 μs (ITU-T K.20/21, 10/700 μs voltage wave shape, single)		TTOW	±350	
5/320 μs (TIA-968-A, 9/720 μs voltage waveshape, single)			±350 ±250	
10/560 µs (TIA-968-A, 10/560 µs voltage wave shape) 10/1000 µs (GR-1089-CORE, 10/1000 µs voltage wave shape)			±250 ±200	
			±200	
Non-repetitive peak on-state current (see Notes 1 and 2)			50	
20 ms, 50 Hz (full sine wave)		ITSM	50	A
nitial rate of rise of on-state current. Linear current ramp. Maximum ramp value < 50 A		di _T /dt	800	A/µs
Junction temperature		TJ	-40 to +150	°C
Storage temperature range		T _{stg}	-65 to +150	°C

NOTES: 1. Initially the device must be in thermal equilibrium with $T_J = 25$ °C.

2. These non-repetitive rated currents are peak values of either polarity. The surge may be repeated after the device returns to its initial conditions.

Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

	Parameter Test Conditions N			Min	Тур	Max	Unit
I _{DRM}	Repetitive peak off-state current	$V_{D} = V_{DRM}$	T _A = 25 °C T _A = 85 °C			±5 ±10	μA
V _(BO)	AC Breakover voltage	dv/dt = ±250 V/ms, R _{SOURCE} = 300 Ω	 '4070J3BJ '4080J3BJ '4095J3BJ '4115J3BJ '4125J3BJ '4145J3BJ '4165J3BJ '4165J3BJ '4200J3BJ '4219J3BJ '4250J3BJ '4290J3BJ '4350J3BJ '4395J3BJ 			± 70 ± 80 ± 95 ± 115 ± 125 ± 145 ± 165 ± 180 ± 200 ± 219 ± 250 ± 290 ± 350	V

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Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
			'4070J3BJ			±77	
			'4080J3BJ			±88	
			'4095J3BJ			±104	
			'4115J3BJ			±125	
			'4125J3BJ			±135	
		dv/dt ≤ ±1000 V/µs, Linear voltage ramp,	'4145J3BJ			±156	
V _(BO)	Ramp breakover voltage	Maximum ramp value = $\pm 500 \text{ V}$	'4165J3BJ			±177	V
()		di/dt = $\pm 20 \text{ A/}\mu\text{s}$, Linear current ramp, Maximum ramp value = $\pm 10 \text{ A}$	ʻ4180J3BJ ʻ4200J3BJ			±192 ±212	
		$a = \pm 10 \text{ A}$	4200J3BJ			±212 ±231	
			4250J3BJ			±263	
			'4290J3BJ			±303	
			'4350J3BJ			±364	
			'4395J3BJ			±409	
			'4070J3BJ thru '4115J3BJ			±900	
I _(BO)	Breakover current	dv/dt = ±250 V/ms, R_{SOURCE} = 300 Ω	'4125J3BJ thru '4219J3BJ			±800	mA
			'4250J3BJ thru '4395J3BJ			±600	
I _H	Holding current	$I_T = \pm 5 \text{ A, di/dt} = \pm 30 \text{ mA/ms}$		±150		±600	mA
dv/dt	Critical rate of rise of	Linear voltage ramp		±5			kV/µs
awat	off-state voltage	Maximum ramp value < 0.85V _{DRM}		÷			κν/μο
Ι _D	Off-state current	$V_{\rm D} = \pm 50 \text{ V}$	T _A = 85 °C			±10	μA
			'4070J3BJ thru '4115J3BJ		195	235	
		$f = 1 \text{ MHz}, V_d = 1 \text{ V rms}, V_D = 0$	'4125J3BJ thru '4219J3BJ		120	145	
			'4250J3BJ thru '4395J3BJ		105	125	
			'4070J3BJ thru '4115J3BJ		180	215	
		f = 1 MHz, V _d = 1 V rms, V _D = -1 V	'4125J3BJ thru '4219J3BJ		110	132	
			'4250J3BJ thru '4395J3BJ		95	115	
	011		'4070J3BJ thru '4115J3BJ		165	200	. –
CO	Off-state capacitance	f = 1 MHz, V _d = 1 V rms, V _D = -2 V	'4125J3BJ thru '4219J3BJ		100	120	pF
			'4250J3BJ thru '4395J3BJ		90	105	
			'4070J3BJ thru '4115J3BJ		85	100	
		f = 1 MHz, V _d = 1 V rms, V _D = -50 V	'4125J3BJ thru '4219J3BJ		50	60	
			'4250J3BJ thru '4395J3BJ		42	50	
		f = 1 MHz, V _d = 1 V rms, V _D = -100 V	'4125J3BJ thru '4219J3BJ		40	50	
		(see Note 3)	'4250J3BJ thru '4395J3BJ		35	40	

NOTE: 3. To avoid possible clipping, the TISP4125J3BJ is tested with V_D = -98 V.

Thermal Characteristics

Parameter	Test Conditions	Min	Тур	Max	Unit
	EIA/JESD51-3 PCB, I _T = I _{TSM(1000)} (see Note 4)			90	°C/W

NOTE: 4. EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

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Parameter Measurement Information

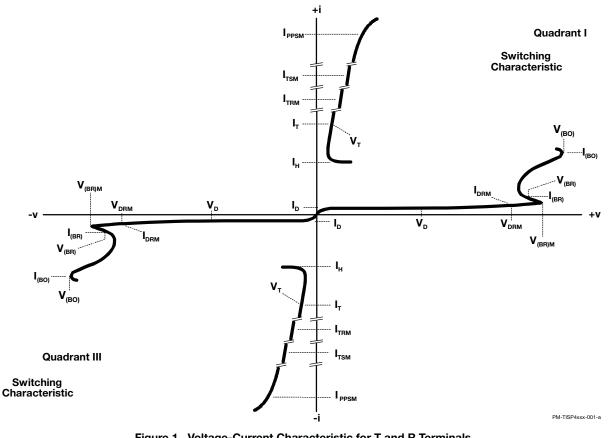
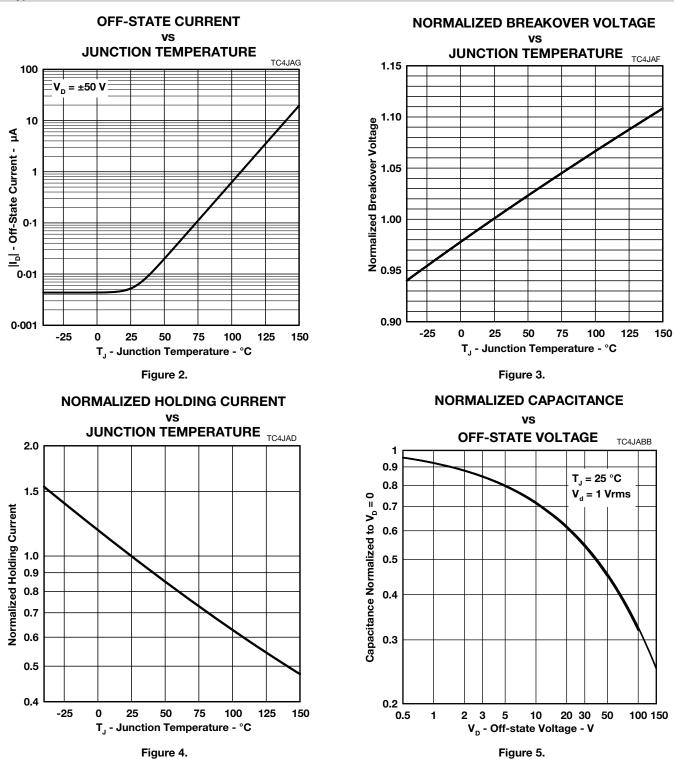


Figure 1. Voltage-Current Characteristic for T and R Terminals All Measurements are Referenced to the R Terminal

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Typical Characteristics

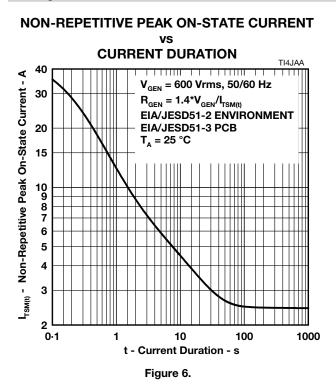


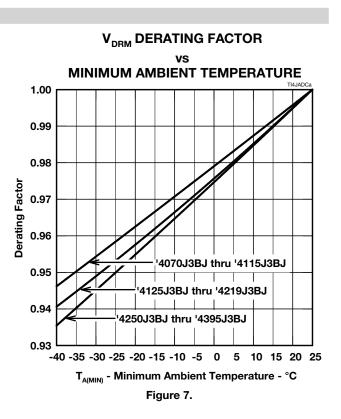
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Rating and Thermal Characteristics





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Applications Information

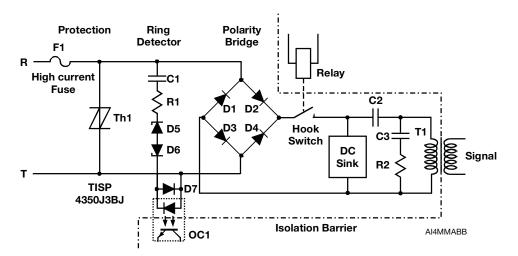


Figure 8. Typical Application Circuit

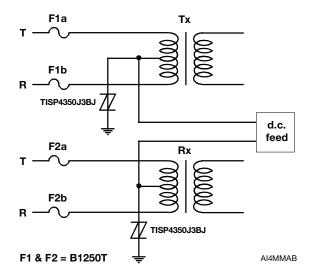


Figure 9. Typical Application Circuit

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